

ABSTRACT OF THE DISCLOSURE

In the method for etching the organic insulating film in which the first RF power is applied to the electrode 12 with the object-to-be-processed having the organic insulating film mounted on and the second RF power is applied to the electrode 14 opposed to the electrode 12, whereby plasma of gas containing NH_3 is generated to etch the organic insulating film, the first RF power and the second RF power are controlled so as to make the Vpp value of the voltage applied to the electrode 12 below 500 V. Thus, the organic insulating film can be vertically processed while the bow amplitude and the corner loss amount of the hard mask are decreased.